



# RF Power Field Effect Transistors

## N-Channel Enhancement-Mode Lateral MOSFETs

Designed for N-CDMA base station applications with frequencies from 1930 to 1990 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN - PCS/cellular radio and WLL applications.

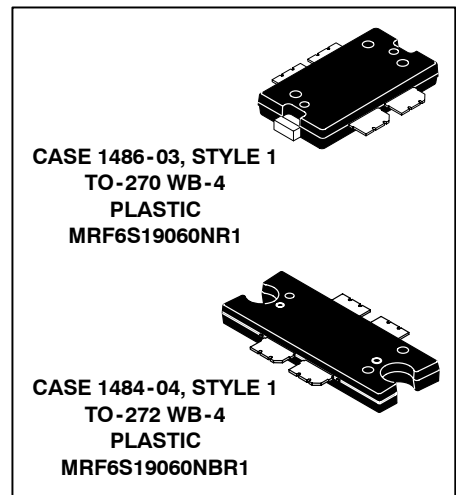
- Typical 2-Carrier N-CDMA Performance:  $V_{DD} = 28$  Volts,  $I_{DQ} = 610$  mA,  $P_{out} = 12$  Watts Avg., Full Frequency Band, IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13) Channel Bandwidth = 1.2288 MHz. PAR = 9.8 dB @ 0.01% Probability on CCDF.  
 Power Gain — 16 dB  
 Drain Efficiency — 26%  
 IM3 @ 2.5 MHz Offset — -37 dBc in 1.2288 MHz Bandwidth  
 ACPR @ 885 kHz Offset — -51 dBc in 30 kHz Bandwidth
- Capable of Handling 5:1 VSWR, @ 28 Vdc, 1960 MHz, 60 Watts CW Output Power

### Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32  $V_{DD}$  Operation
- Integrated ESD Protection
- Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications
- 200°C Capable Plastic Package
- N Suffix Indicates Lead-Free Terminations. RoHS Compliant.
- In Tape and Reel. R1 Suffix = 500 Units per 44 mm, 13 inch Reel.



**1930-1990 MHz, 12 W AVG., 28 V**  
**2 x N-CDMA**  
**LATERAL N-CHANNEL**  
**RF POWER MOSFETs**



**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-0.5, +68	Vdc
Gate-Source Voltage	$V_{GS}$	-0.5, +12	Vdc
Storage Temperature Range	$T_{stg}$	- 65 to +175	°C
Operating Junction Temperature	$T_J$	200	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 81°C, 60 W CW Case Temperature 79°C, 12 W CW	$R_{\theta JC}$	0.84 1.0	°C/W

1. MTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22-A114)	1B (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	III (Minimum)

**Table 4. Moisture Sensitivity Level**

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD 22-A113, IPC/JEDEC J-STD-020	3	260	°C

**Table 5. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**Off Characteristics**

Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 68\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	10	$\mu\text{Adc}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	1	$\mu\text{Adc}$
Gate-Source Leakage Current ( $V_{GS} = 5\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	—	—	1	$\mu\text{Adc}$

**On Characteristics**

Gate Threshold Voltage ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 200\ \mu\text{Adc}$ )	$V_{GS(th)}$	1.5	2.2	2.5	Vdc
Gate Quiescent Voltage ( $V_{DS} = 28\text{ Vdc}$ , $I_D = 610\text{ mAdc}$ )	$V_{GS(Q)}$	2	2.8	4	Vdc
Drain-Source On-Voltage ( $V_{GS} = 10\text{ Vdc}$ , $I_D = 2.0\text{ Adc}$ )	$V_{DS(on)}$	0.2	0.3	0.4	Vdc

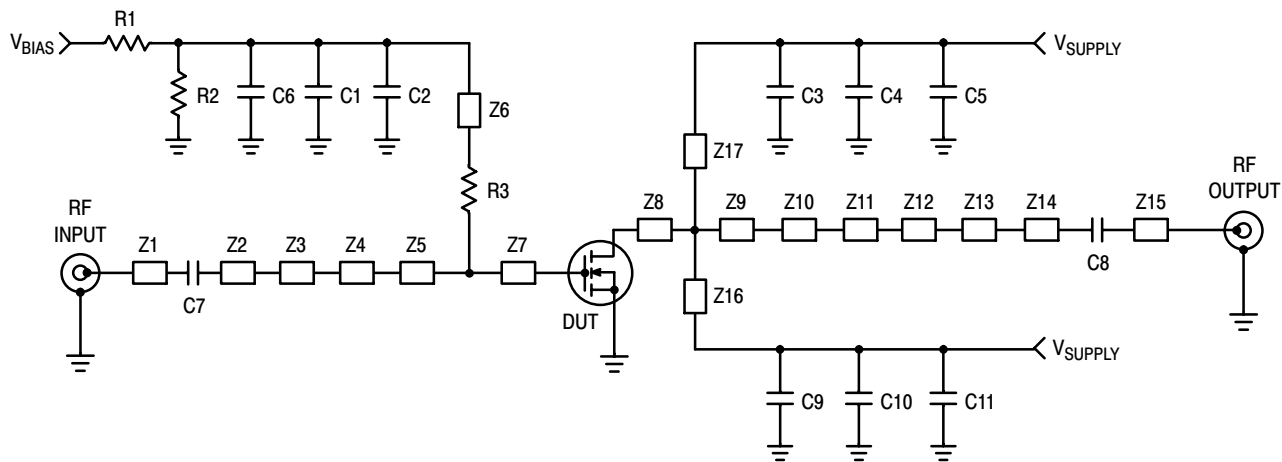
**Dynamic Characteristics** <sup>(1)</sup>

Reverse Transfer Capacitance ( $V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{rss}$	—	1.5	—	pF
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**Functional Tests** (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 610\text{ mA}$ ,  $P_{out} = 12\text{ W Avg.}$ ,  $f_1 = 1930\text{ MHz}$ ,  $f_2 = 1932.5\text{ MHz}$  and  $f_1 = 1987.5\text{ MHz}$ ,  $f_2 = 1990\text{ MHz}$ , 2-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carriers. ACPR measured in 30 kHz Channel Bandwidth @  $\pm 885\text{ kHz}$  Offset. IM3 measured in 1.2288 MHz Channel Bandwidth @  $\pm 2.5\text{ MHz}$  Offset. PAR = 9.8 dB @ 0.01% Probability on CCDF.

Power Gain	$G_{ps}$	14.5	16	18.5	dB
Drain Efficiency	$\eta_D$	24.5	26	—	%
Intermodulation Distortion	IM3	—	-37	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-51	-48	dBc
Input Return Loss	IRL	—	-12	-10	dB

1. Part is internally matched both on input and output.



Z1	0.250" x 0.083" Microstrip	Z11	0.225" x 0.083" Microstrip
Z2	0.750" x 0.083" Microstrip	Z12	0.325" x 0.500" Microstrip
Z3	0.375" x 0.425" Microstrip	Z13	0.450" x 0.083" Microstrip
Z4	0.370" x 0.083" Microstrip	Z14	0.300" x 0.245" Microstrip
Z5	0.365" x 1.000" Microstrip	Z15	0.195" x 0.083" Microstrip
Z6	0.650" x 0.080" Microstrip	Z16	1.150" x 0.070" Microstrip
Z7, Z8	0.115" x 1.000" Microstrip	Z17	1.150" x 0.083" Microstrip
Z9	0.240" x 1.000" Microstrip	PCB	Arlon AD250, 0.030", $\epsilon_r = 2.5$
Z10	0.310" x 0.315" Microstrip		

**Figure 1. MRF6S19060NR1(NBR1) Test Circuit Schematic**

**Table 6. MRF6S19060NR1(NBR1) Test Circuit Component Designations and Values**

Part	Description	Part Number	Manufacturer
C1	100 nF Chip Capacitor	CDR33BX104AKWS	Kemet
C2, C3, C7, C8, C9	6.8 pF Chip Capacitors	600B6R8BT250XT	ATC
C4, C5, C6, C10, C11	10 $\mu$ F, 50 V Chip Capacitors	GRM55DR61H106KA88L	Murata
R1	1 k $\Omega$ Chip Resistor		
R2	10 k $\Omega$ Chip Resistor		
R3	10 $\Omega$ Chip Resistor		

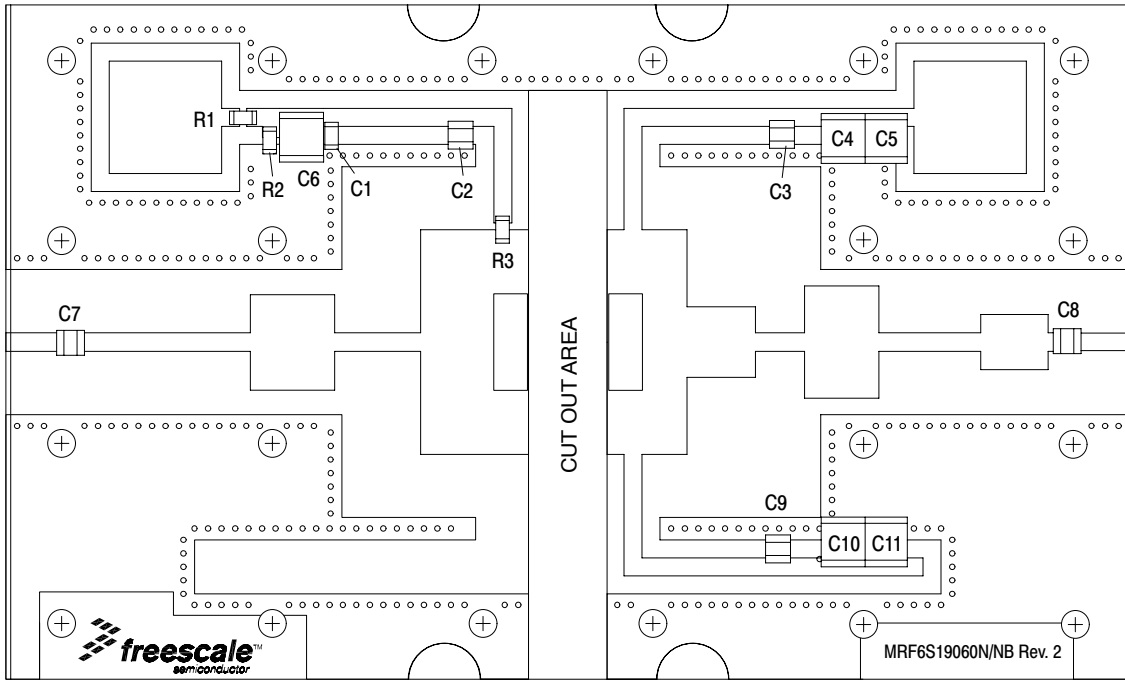


Figure 2. MRF6S19060NR1(NBR1) Test Circuit Component Layout

## TYPICAL CHARACTERISTICS

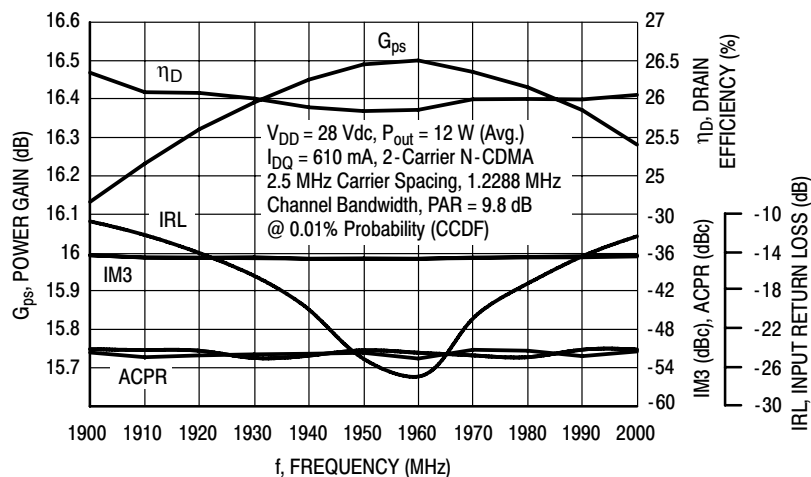


Figure 3. 2-Carrier N-CDMA Broadband Performance @  $P_{out} = 12$  Watts Avg.

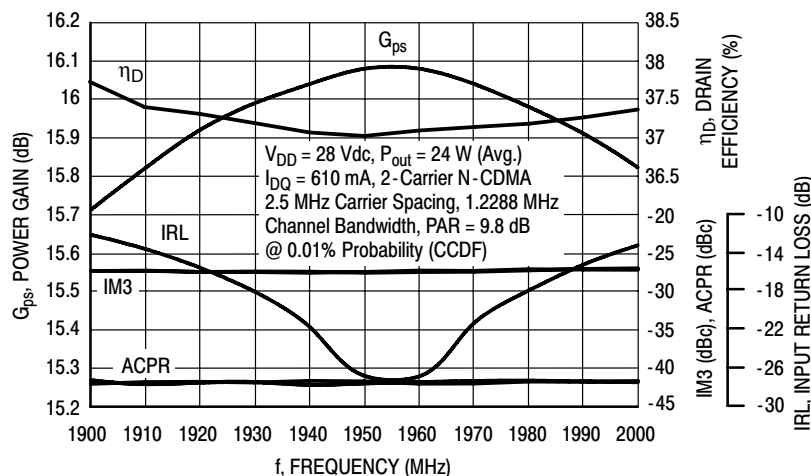


Figure 4. 2-Carrier N-CDMA Broadband Performance @  $P_{out} = 24$  Watts Avg.

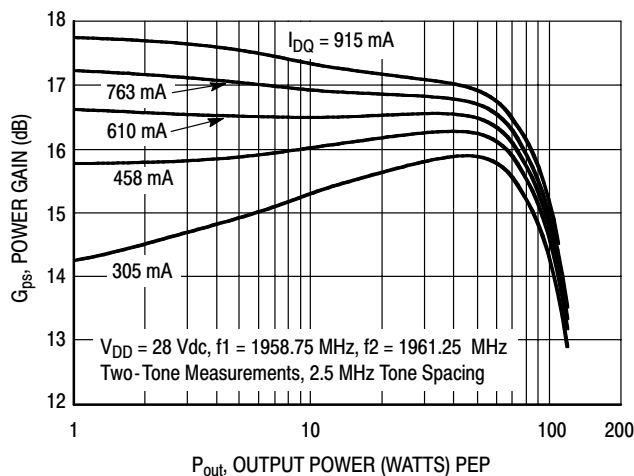


Figure 5. Two-Tone Power Gain versus Output Power

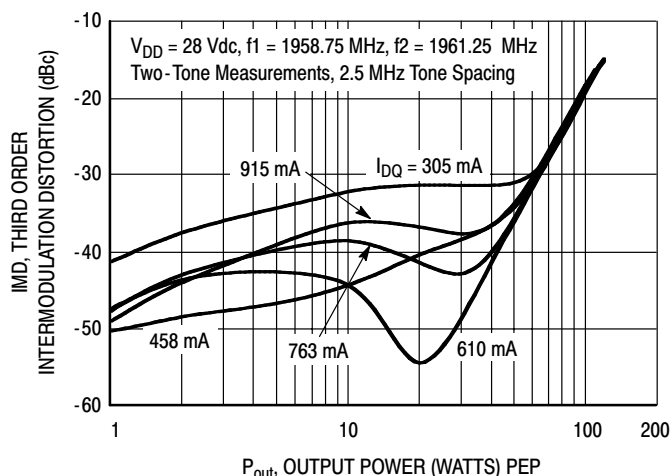
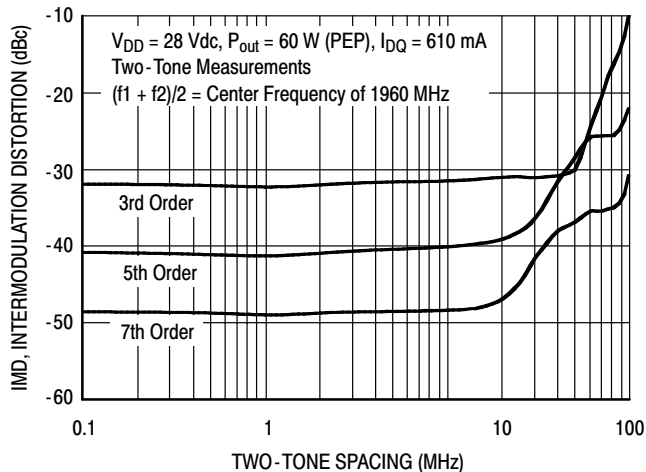
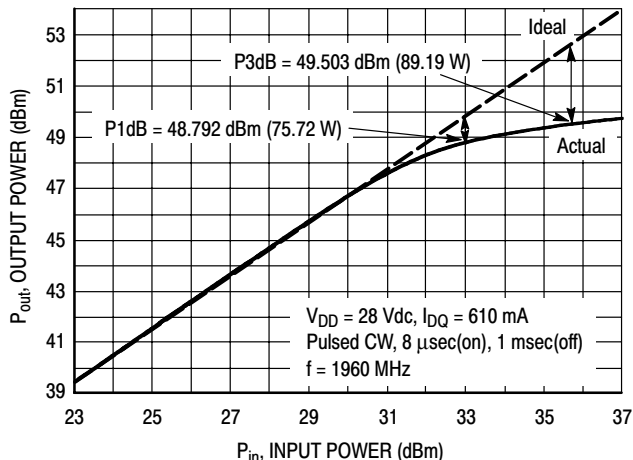


Figure 6. Third Order Intermodulation Distortion versus Output Power

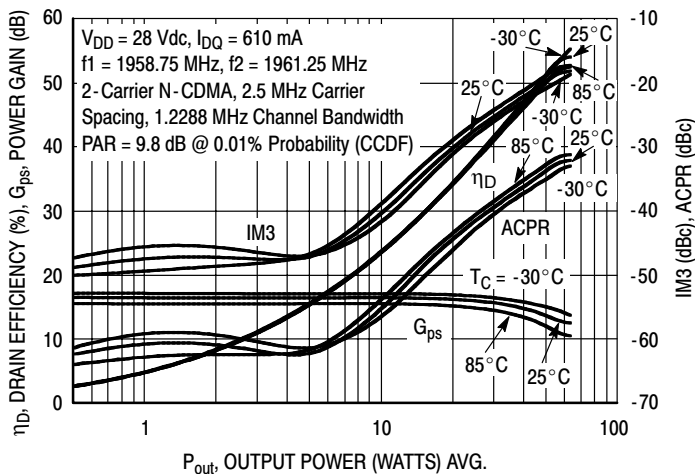
## TYPICAL CHARACTERISTICS



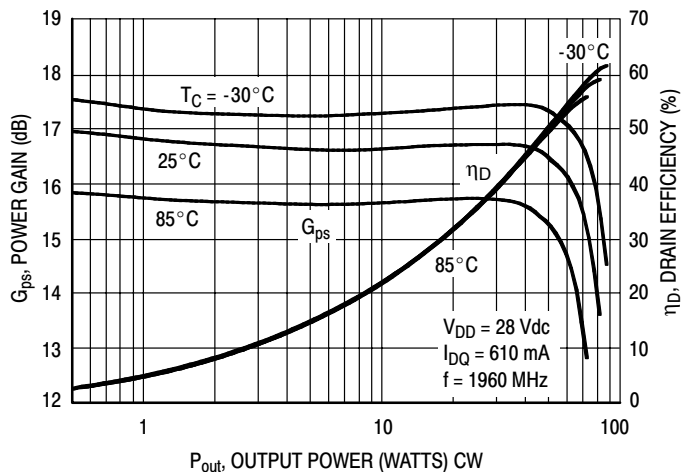
**Figure 7. Intermodulation Distortion Products versus Tone Spacing**



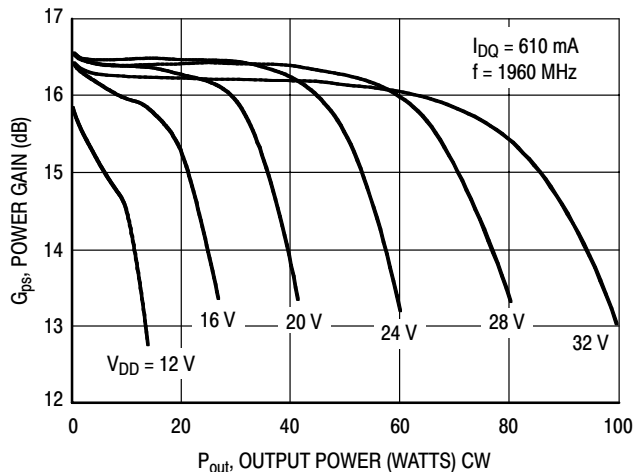
**Figure 8. Pulse CW Output Power versus Input Power**



**Figure 9. 2-Carrier N-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power**



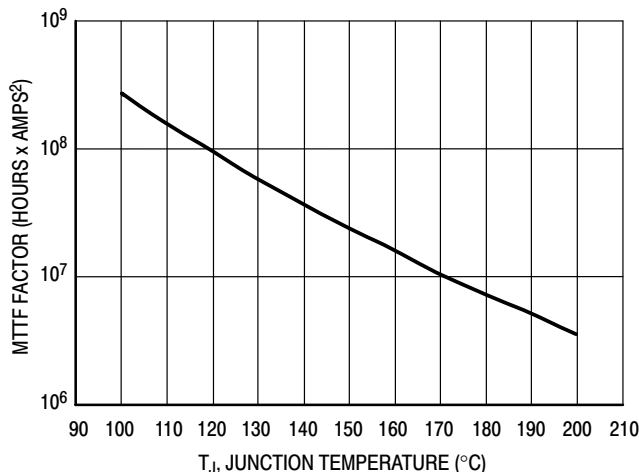
**Figure 10. Power Gain and Drain Efficiency versus CW Output Power**



**Figure 11. Power Gain versus Output Power**

MRF6S19060NR1 MRF6S19060NBR1

## TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours x ampere<sup>2</sup> drain current. Life tests at elevated temperatures have correlated to better than ±10% of the theoretical prediction for metal failure. Divide MTTF factor by  $I_D^2$  for MTTF in a particular application.

Figure 12. MTTF Factor versus Junction Temperature

## N-CDMA TEST SIGNAL

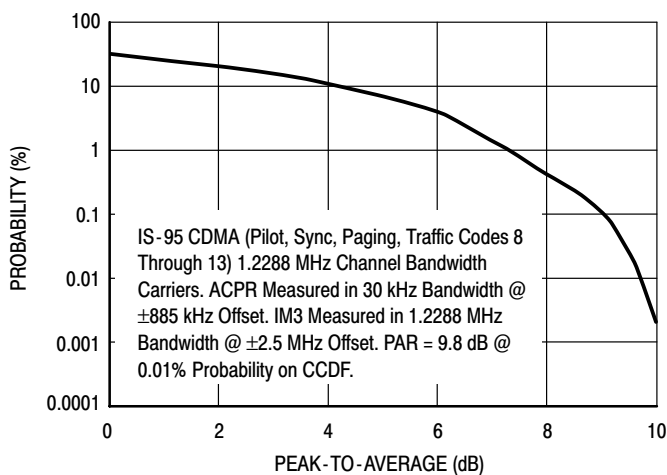


Figure 13. 2-Carrier CCDF N-CDMA

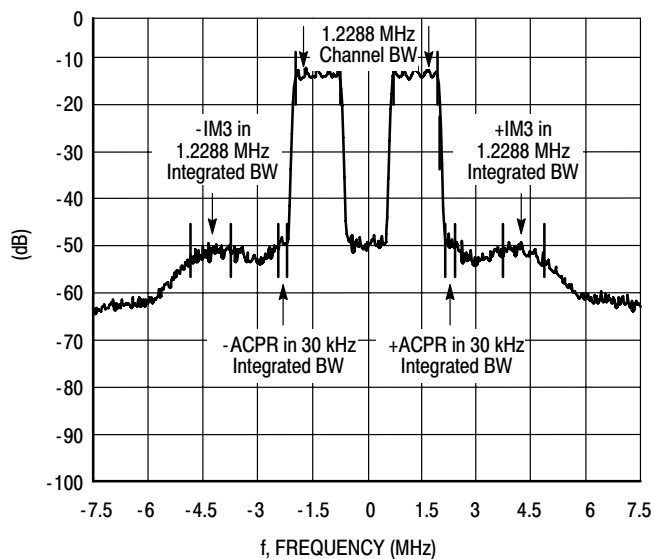
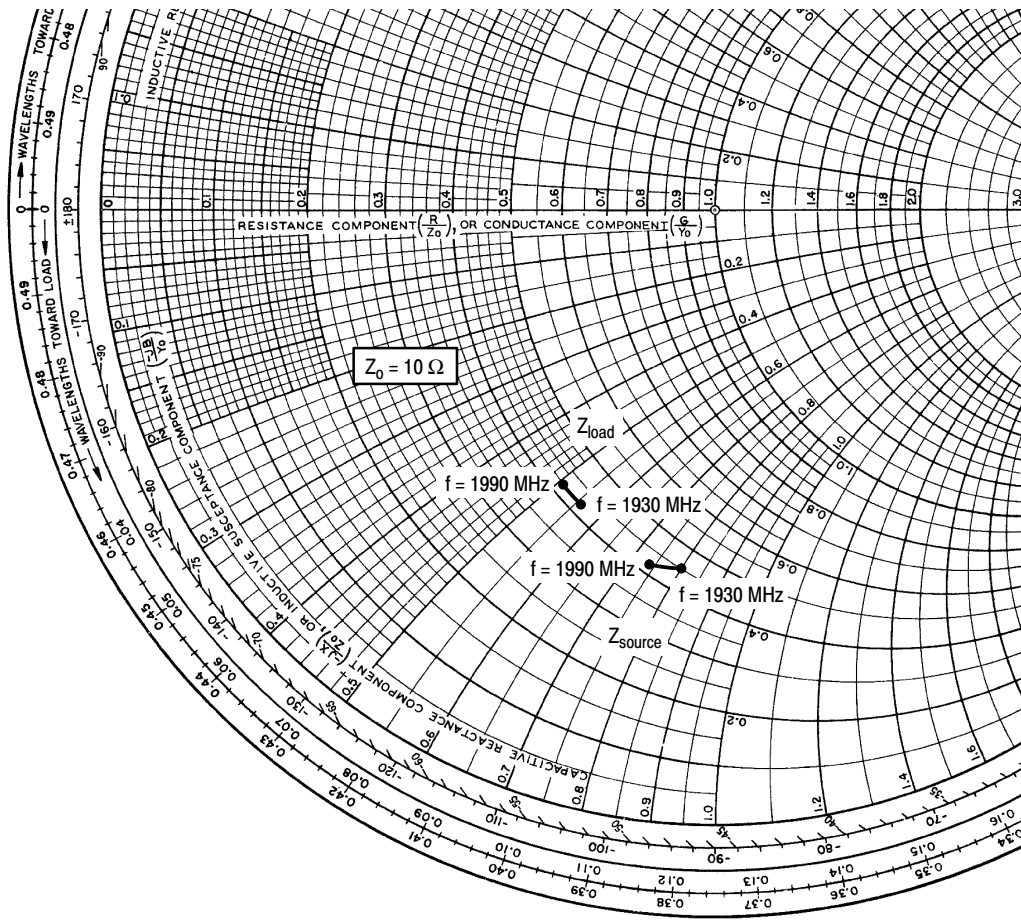


Figure 14. 2-Carrier N-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$ ,  $I_{DQ} = 610 \text{ mA}$ ,  $P_{out} = 12 \text{ W Avg.}$

f MHz	$Z_{source}$ $\Omega$	$Z_{load}$ $\Omega$
1930	$4.54 - j7.95$	$4.15 - j5.58$
1960	$4.33 - j7.74$	$4.17 - j5.34$
1990	$4.20 - j7.43$	$4.22 - j5.10$

$Z_{source}$  = Test circuit impedance as measured from gate to ground.

$Z_{load}$  = Test circuit impedance as measured from drain to ground.

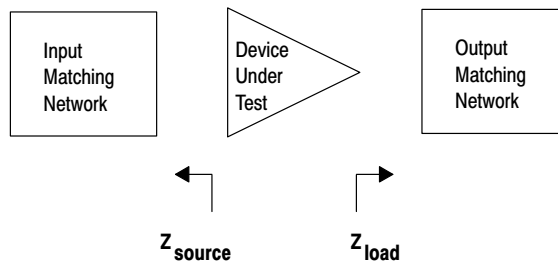


Figure 15. Series Equivalent Source and Load Impedance

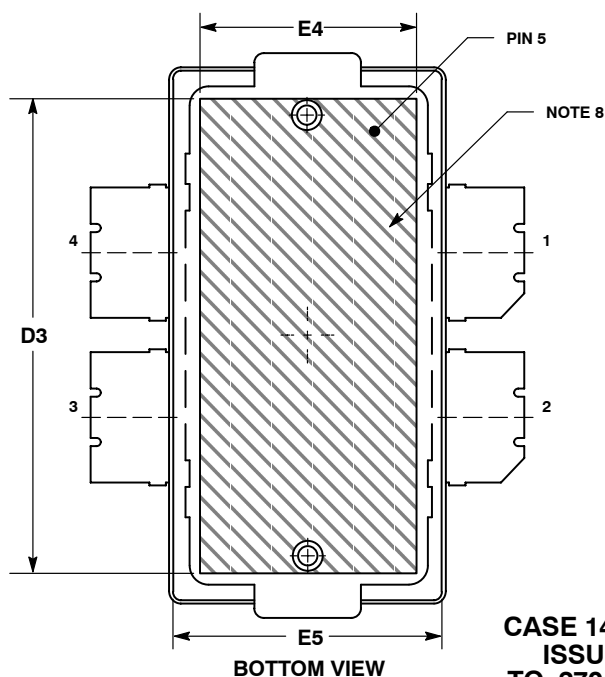
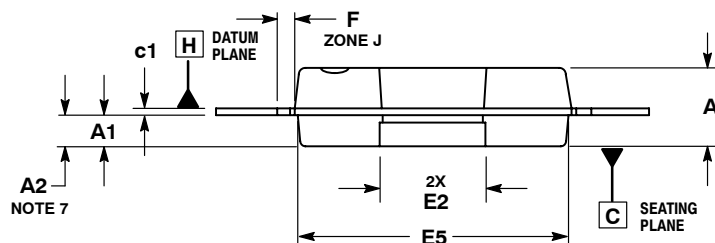
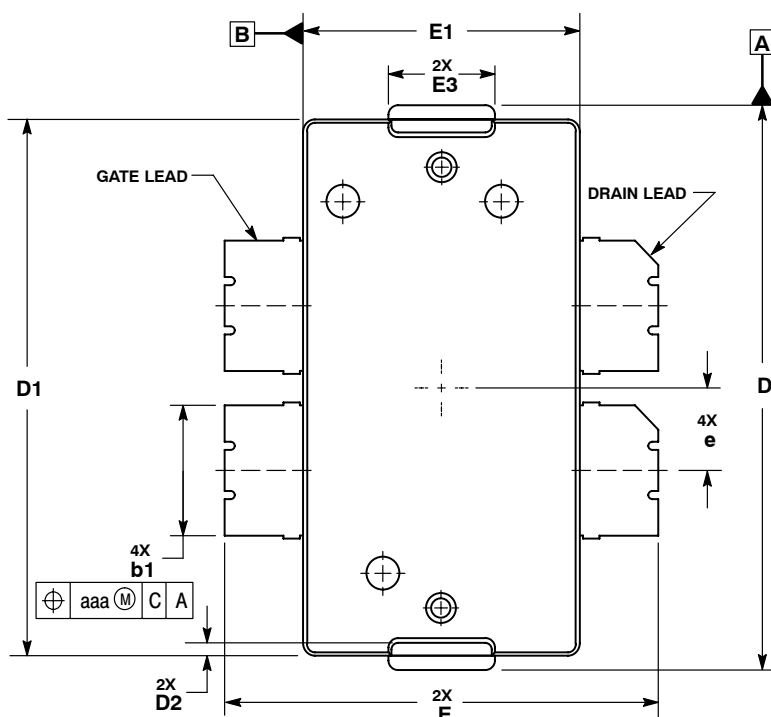


# NOTES

# NOTES

# NOTES

# PACKAGE DIMENSIONS



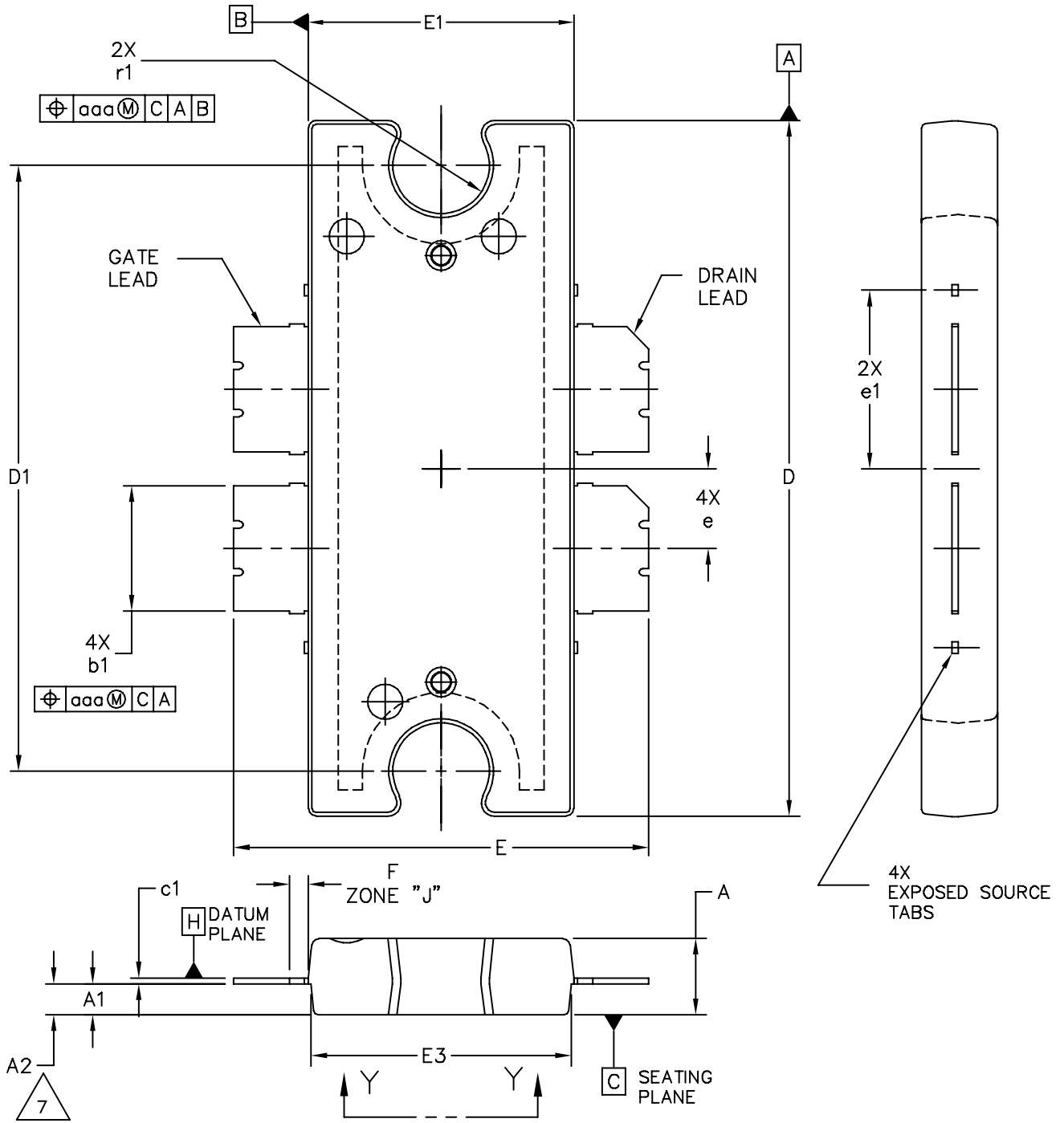
- NOTES:
1. CONTROLLING DIMENSION: INCH.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
  3. DATUM PLANE -H- IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
  4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
  5. DIMENSION "b1" DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b1" DIMENSION AT MAXIMUM MATERIAL CONDITION.
  6. DATUMS -A- AND -B- TO BE DETERMINED AT DATUM PLANE -H-.
  7. DIMENSION A2 APPLIES WITHIN ZONE "J" ONLY.
  8. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64
A1	.039	.043	0.99	1.09
A2	.040	.042	1.02	1.07
D	.712	.720	18.08	18.29
D1	.688	.692	17.48	17.58
D2	.011	.019	0.28	0.48
D3	.600	---	15.24	---
E	.551	.559	14	14.2
E1	.353	.357	8.97	9.07
E2	.132	.140	3.35	3.56
E3	.124	.132	3.15	3.35
E4	.270	---	6.86	---
E5	.346	.350	8.79	8.89
F	.025 BSC		0.64 BSC	
b1	.164	.170	4.17	4.32
c1	.007	.011	0.18	0.28
e	.106 BSC		2.69 BSC	
aaa	.004		0.10	

- STYLE 1:  
 PIN 1. DRAIN  
 2. DRAIN  
 3. GATE  
 4. GATE  
 5. SOURCE

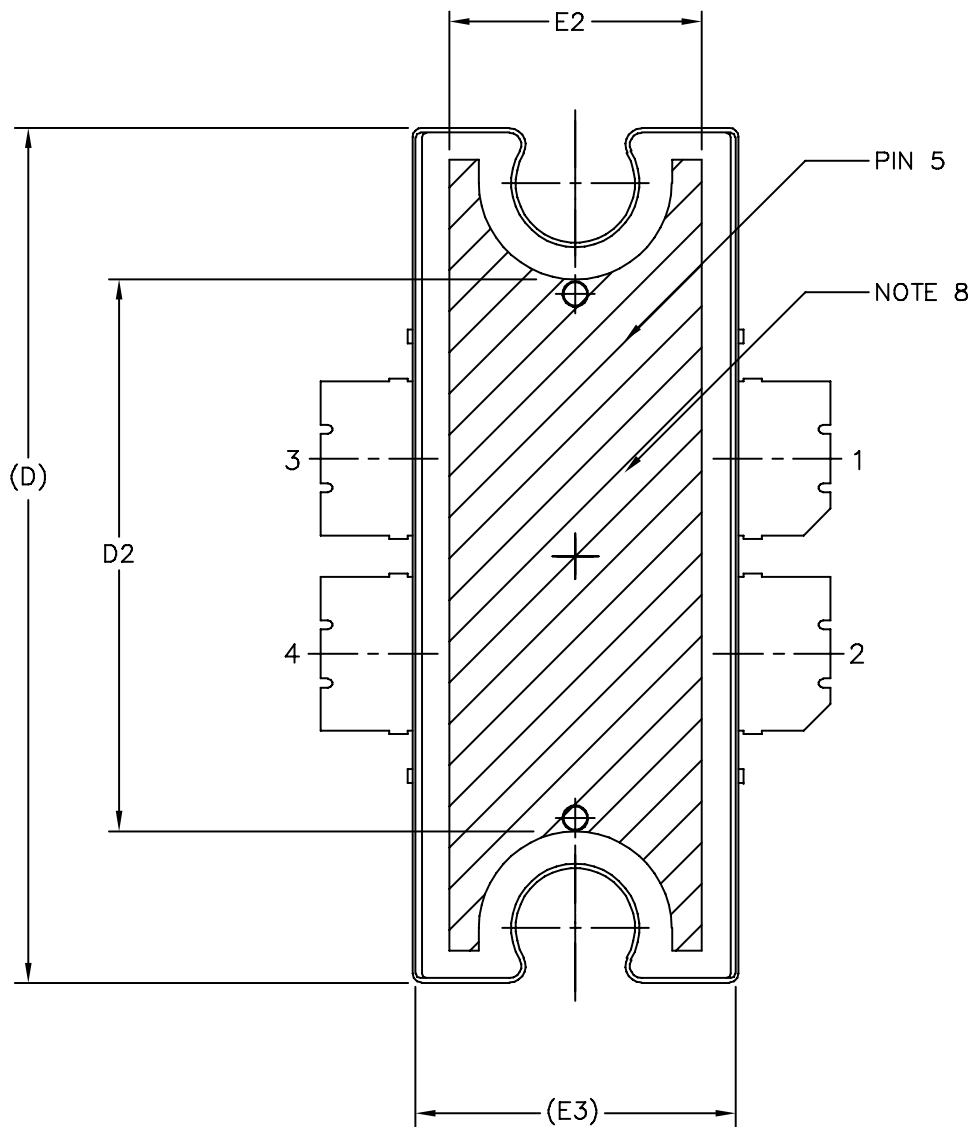
**CASE 1486-03  
 ISSUE C  
 TO-270 WB-4  
 PLASTIC  
 MRF6S19060NR1**

MRF6S19060NR1 MRF6S19060NBR1



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TITLE:  TO-272 4 LEAD, WIDE BODY			DOCUMENT NO: 98ASA10575D		REV: D
			CASE NUMBER: 1484-04		05 APR 2006
			STANDARD: NON-JEDEC		

MRF6S19060NR1 MRF6S19060NBR1



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	CASE NUMBER: 1484-04	05 APR 2006	
	STANDARD: NON-JEDEC		

NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE H IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.
5. DIMENSIONS "b1" DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b1" DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
7. DIMENSION A2 APPLIES WITHIN ZONE "J" ONLY.
8. HATCHING REPRESENTS EXPOSED AREA OF THE HEAT SLUG. HATCHED AREA SHOWN IS ON THE SAME PLANE.

STYLE 1:

PIN 1 - DRAIN      PIN 2 - DRAIN  
 PIN 3 - GATE      PIN 4 - GATE  
 PIN 5 - SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64	b1	.164	.170	4.17	4.32
A1	.039	.043	0.99	1.09	c1	.007	.011	.18	.28
A2	.040	.042	1.02	1.07	r1	.063	.068	1.60	1.73
D	.928	.932	23.57	23.67	e	.106 BSC		2.69 BSC	
D1	.810 BSC		20.57 BSC		e1	.239 INFO ONLY		6.07 INFO ONLY	
D2	.600	---	15.24	---	aaa	.004		.10	
E	.551	.559	14	14.2					
E1	.353	.357	8.97	9.07					
E2	.270	---	6.86	---					
E3	.346	.350	8.79	8.89					
F	.025 BSC		0.64 BSC						

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		CASE NUMBER: 1484-04		05 APR 2006	
		STANDARD: NON-JEDEC			

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